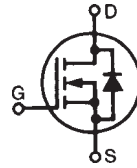


# Polar™ HiPerFET™

# IXFN32N120P

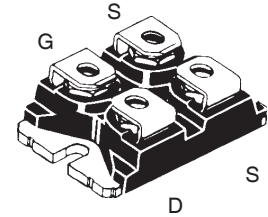
## Power MOSFET

N-Channel Enhancement Mode  
Avalanche Rated  
Fast Intrinsic Diode



$V_{DSS} = 1200V$   
 $I_{D25} = 32A$   
 $R_{DS(on)} \leq 310m\Omega$   
 $t_{rr} \leq 300ns$

miniBLOC  
 E153432



G = Gate      D = Drain  
 S = Source

Either Source Terminal S can be used as the Source Terminal or the Kelvin Source ( Gate Return ) Terminal.

| Symbol        | Test Conditions                                                    | Maximum Ratings |            |
|---------------|--------------------------------------------------------------------|-----------------|------------|
| $V_{DSS}$     | $T_J = 25^\circ C$ to $150^\circ C$                                | 1200            | V          |
| $V_{DGR}$     | $T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$          | 1200            | V          |
| $V_{GSS}$     | Continuous                                                         | $\pm 30$        | V          |
| $V_{GSM}$     | Transient                                                          | $\pm 40$        | V          |
| $I_{D25}$     | $T_C = 25^\circ C$                                                 | 32              | A          |
| $I_{DM}$      | $T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$               | 100             | A          |
| $I_A$         | $T_C = 25^\circ C$                                                 | 16              | A          |
| $E_{AS}$      | $T_C = 25^\circ C$                                                 | 2               | J          |
| $dv/dt$       | $I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ C$ | 20              | V/ns       |
| $P_D$         | $T_C = 25^\circ C$                                                 | 1000            | W          |
| $T_J$         |                                                                    | -55 ... +150    | $^\circ C$ |
| $T_{JM}$      |                                                                    | 150             | $^\circ C$ |
| $T_{stg}$     |                                                                    | -55 ... +150    | $^\circ C$ |
| $T_L$         | 1.6mm (0.062 in.) from Case for 10s                                | 300             | $^\circ C$ |
| $T_{SOLD}$    | Plastic Body for 10s                                               | 260             | $^\circ C$ |
| $V_{ISOL}$    | 50/60 Hz, RMS $t = 1$ minute                                       | 2500            | V~         |
|               | $I_{ISOL} \leq 1mA$ $t = 1$ second                                 | 3000            | V~         |
| $M_d$         | Mounting Torque                                                    | 1.5/13          | Nm/lb.in.  |
|               | Terminal Connection Torque                                         | 1.3/11.5        | Nm/lb.in.  |
| <b>Weight</b> |                                                                    | 30              | g          |

### Features

- International Standard Package
- miniBLOC, with Aluminium Nitride Isolation
- Isolation Voltage 2500 V~
- High Current Handling Capability
- Fast Intrinsic Diode
- Avalanche Rated
- Low  $R_{DS(on)}$  HDMOST™ Process

### Advantages

- Easy to Mount
- Space Savings
- High Power Density

### Applications

- High Voltage Switch-Mode and Resonant-Mode Power Supplies
- High Voltage Pulse Power Applications
- High Voltage Discharge Circuits in Lasers Pulsers, Spark Igniters, RF Generators
- High Voltage DC-DC Converters
- High Voltage DC-AC Inverters

| Symbol       | Test Conditions<br>( $T_J = 25^\circ C$ , Unless Otherwise Specified) | Characteristic Values |      |                    |
|--------------|-----------------------------------------------------------------------|-----------------------|------|--------------------|
|              |                                                                       | Min.                  | Typ. | Max.               |
| $BV_{DSS}$   | $V_{GS} = 0V$ , $I_D = 3mA$                                           | 1200                  |      | V                  |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$ , $I_D = 1mA$                                       | 3.5                   |      | 6.5 V              |
| $I_{GSS}$    | $V_{GS} = \pm 30V$ , $V_{DS} = 0V$                                    |                       |      | $\pm 300$ nA       |
| $I_{DSS}$    | $V_{DS} = V_{DSS}$ , $V_{GS} = 0V$<br>$T_J = 125^\circ C$             |                       |      | 50 $\mu A$<br>5 mA |
| $R_{DS(on)}$ | $V_{GS} = 10V$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1                   |                       |      | 310 m $\Omega$     |

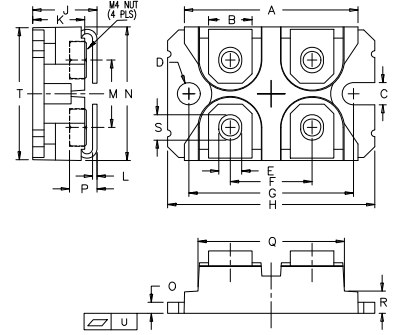
| Symbol       | Test Conditions<br>( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)                                                                        | Characteristic Values |       |                    |
|--------------|----------------------------------------------------------------------------------------------------------------------------------------------------|-----------------------|-------|--------------------|
|              |                                                                                                                                                    | Min.                  | Typ.  | Max.               |
| $g_{fs}$     | $V_{DS} = 20\text{V}$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1                                                                                         | 17                    | 28    | S                  |
| $C_{iss}$    | $V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$                                                                                   |                       | 21    | nF                 |
| $C_{oss}$    |                                                                                                                                                    |                       | 1100  | pF                 |
| $C_{rss}$    |                                                                                                                                                    |                       | 77    | pF                 |
| $R_{Gi}$     | Gate input resistance                                                                                                                              |                       | 0.84  | $\Omega$           |
| $t_{d(on)}$  | <b>Resistive Switching Times</b><br>$V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$<br>$R_G = 1\Omega$ (External) |                       | 70    | ns                 |
| $t_r$        |                                                                                                                                                    |                       | 62    | ns                 |
| $t_{d(off)}$ |                                                                                                                                                    |                       | 88    | ns                 |
| $t_f$        |                                                                                                                                                    |                       | 58    | ns                 |
| $Q_{g(on)}$  | $V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$                                                                   |                       | 360   | nC                 |
| $Q_{gs}$     |                                                                                                                                                    |                       | 130   | nC                 |
| $Q_{gd}$     |                                                                                                                                                    |                       | 160   | nC                 |
| $R_{thJC}$   |                                                                                                                                                    |                       | 0.125 | $^\circ\text{C/W}$ |
| $R_{thCS}$   |                                                                                                                                                    | 0.05                  |       | $^\circ\text{C/W}$ |

### Source-Drain Diode

| Symbol   | Test Conditions<br>( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)                           | Characteristic Values |      |               |
|----------|-------------------------------------------------------------------------------------------------------|-----------------------|------|---------------|
|          |                                                                                                       | Min.                  | Typ. | Max.          |
| $I_S$    | $V_{GS} = 0\text{V}$                                                                                  |                       |      | 32 A          |
| $I_{SM}$ | Repetitive, Pulse Width Limited by $T_{JM}$                                                           |                       |      | 128 A         |
| $V_{SD}$ | $I_F = I_S$ , $V_{GS} = 0\text{V}$ , Note 1                                                           |                       |      | 1.5 V         |
| $t_{rr}$ | $I_F = 20\text{A}$ , $-di/dt = 100\text{A}/\mu\text{s}$<br>$V_R = 100\text{V}$ , $V_{GS} = 0\text{V}$ |                       |      | 300 ns        |
| $Q_{RM}$ |                                                                                                       |                       | 1.9  | $\mu\text{C}$ |
| $I_{RM}$ |                                                                                                       |                       | 15   | A             |

Note 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

### SOT-227B (IXFN) Outline



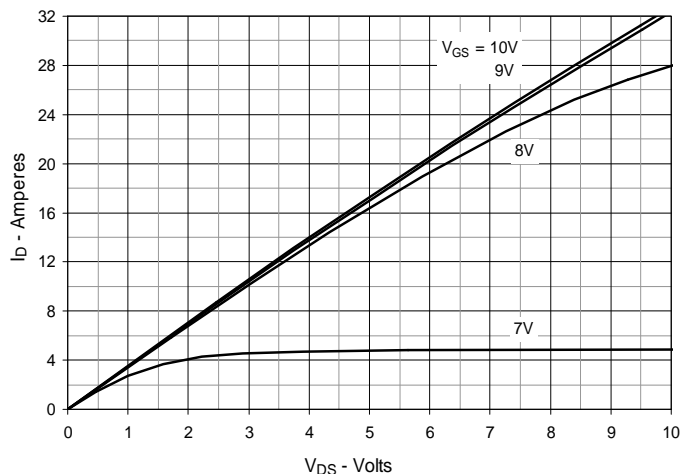
(M4 screws (4x) supplied)

| SYM | INCHES |       | MILLIMETERS |       |
|-----|--------|-------|-------------|-------|
|     | MIN    | MAX   | MIN         | MAX   |
| A   | 1.240  | 1.255 | 31.50       | 31.88 |
| B   | .307   | .323  | 7.80        | 8.20  |
| C   | .161   | .169  | 4.09        | 4.29  |
| D   | .161   | .169  | 4.09        | 4.29  |
| E   | .161   | .169  | 4.09        | 4.29  |
| F   | .587   | .595  | 14.91       | 15.11 |
| G   | 1.186  | 1.193 | 30.12       | 30.30 |
| H   | 1.496  | 1.505 | 38.00       | 38.23 |
| J   | .460   | .481  | 11.68       | 12.22 |
| K   | .351   | .378  | 8.92        | 9.60  |
| L   | .030   | .033  | 0.76        | 0.84  |
| M   | .496   | .506  | 12.60       | 12.85 |
| N   | .990   | 1.001 | 25.15       | 25.42 |
| O   | .078   | .084  | 1.98        | 2.13  |
| P   | .195   | .235  | 4.95        | 5.97  |
| Q   | 1.045  | 1.059 | 26.54       | 26.90 |
| R   | .155   | .174  | 3.94        | 4.42  |
| S   | .186   | .191  | 4.72        | 4.85  |
| T   | .968   | .987  | 24.59       | 25.07 |
| U   | -.002  | .004  | -0.05       | 0.1   |

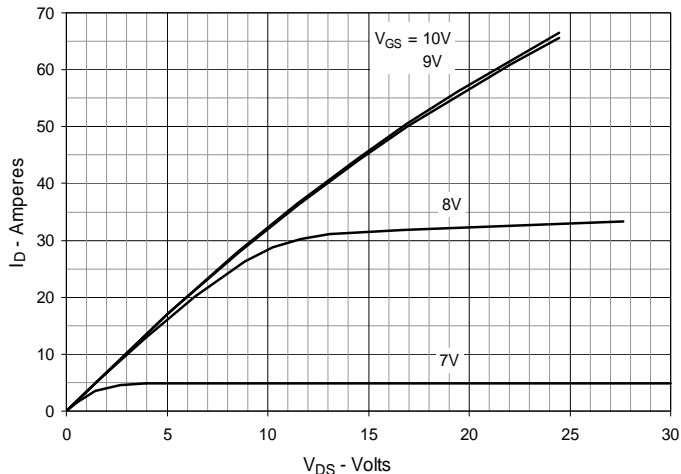
IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

|                                                                                  |           |           |           |           |              |              |              |              |              |             |
|----------------------------------------------------------------------------------|-----------|-----------|-----------|-----------|--------------|--------------|--------------|--------------|--------------|-------------|
| IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: | 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665    | 6,404,065 B1 | 6,683,344    | 6,727,585    | 7,005,734 B2 | 7,157,338B2 |
|                                                                                  | 4,850,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123 B1 | 6,534,343    | 6,710,405 B2 | 6,759,692    | 7,063,975 B2 |             |
|                                                                                  | 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505    | 6,710,463    | 6,771,478 B2 | 7,071,537    |             |

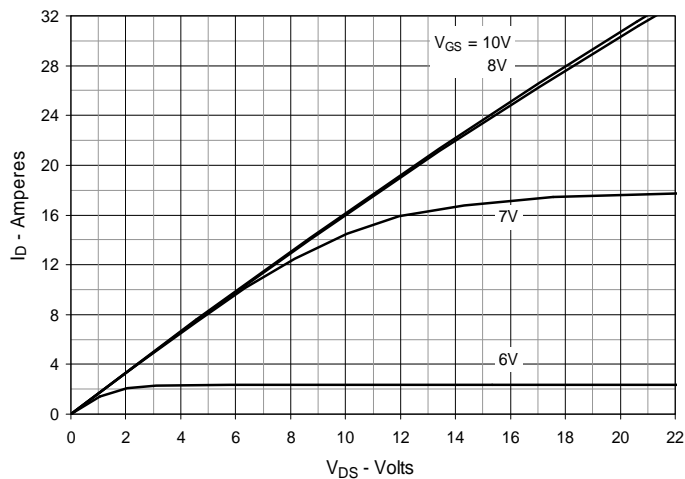
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



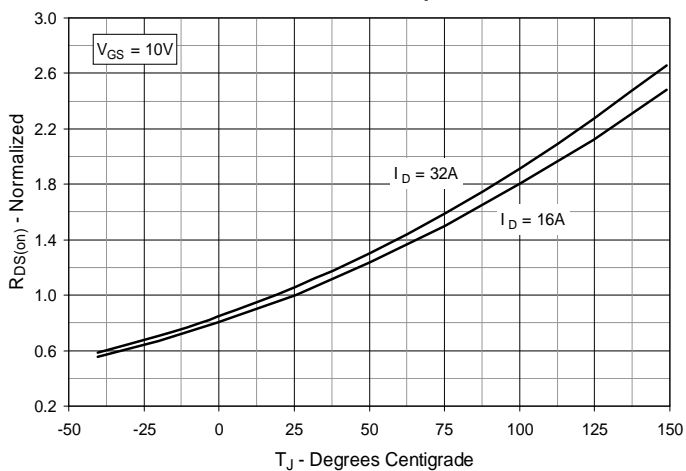
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



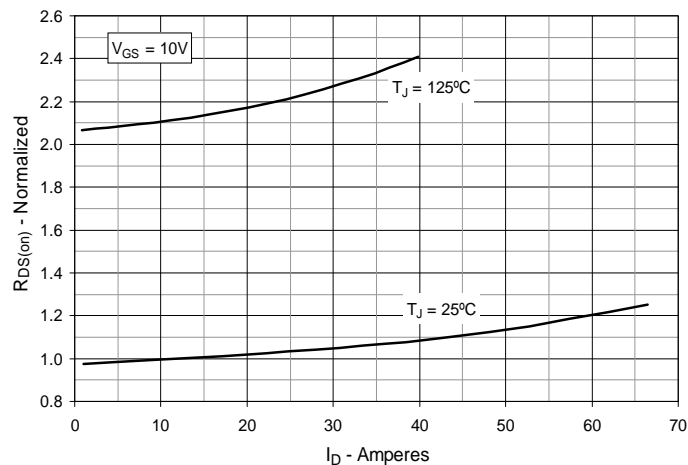
**Fig. 3. Output Characteristics  $T_J = 125^\circ\text{C}$**



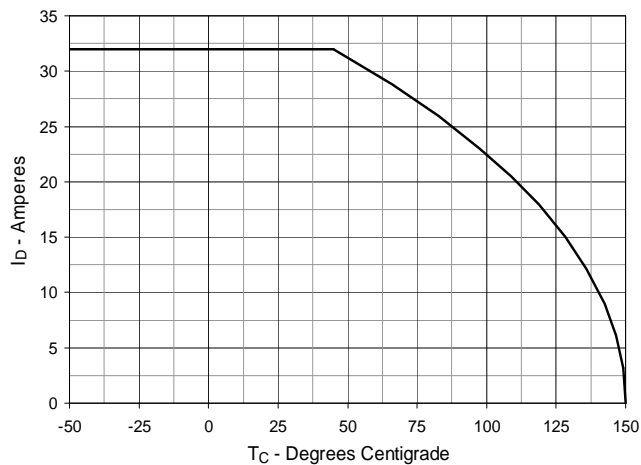
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 16\text{A}$  Value vs. Junction Temperature**



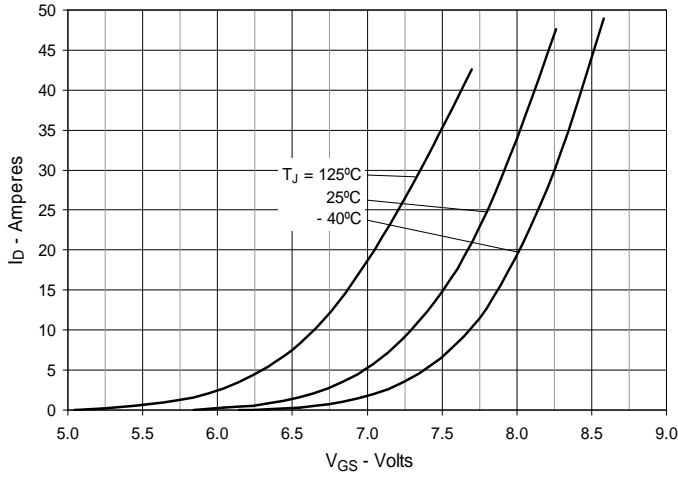
**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 16\text{A}$  Value vs. Drain Current**



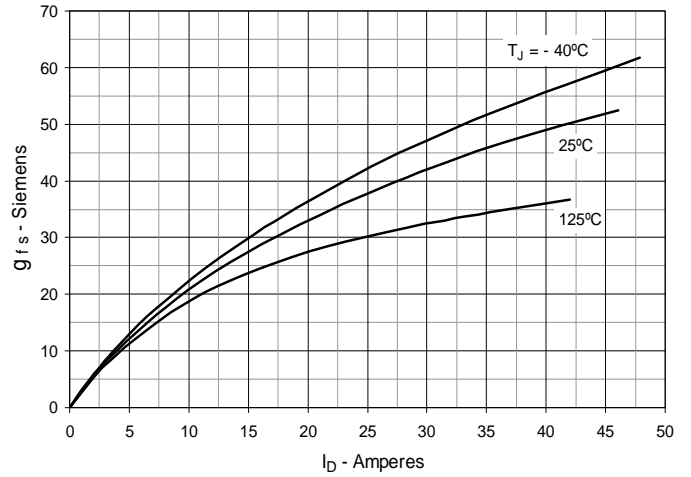
**Fig. 6. Maximum Drain Current vs. Case Temperature**



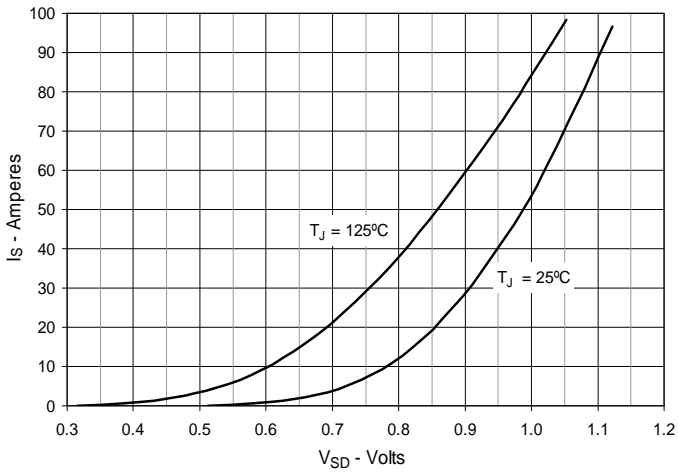
**Fig. 7. Input Admittance**



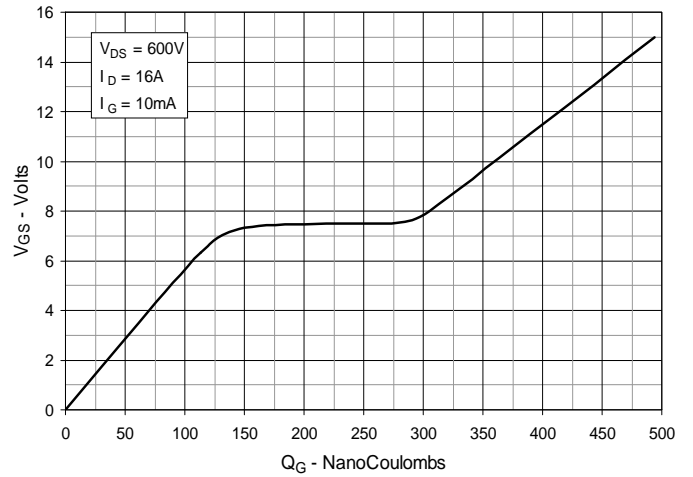
**Fig. 8. Transconductance**



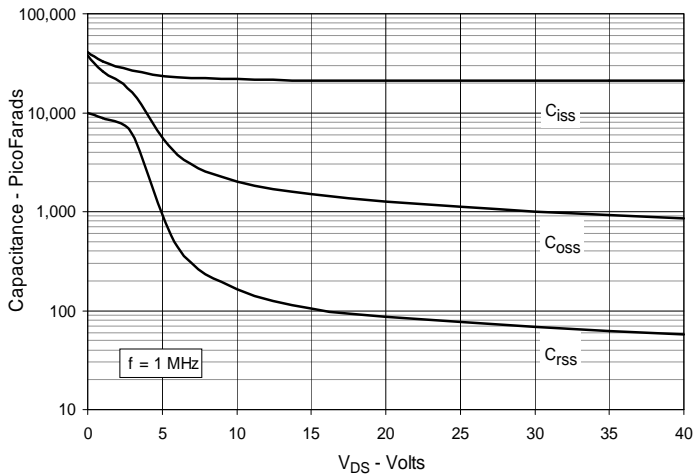
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Forward-Bias Safe Operating Area**

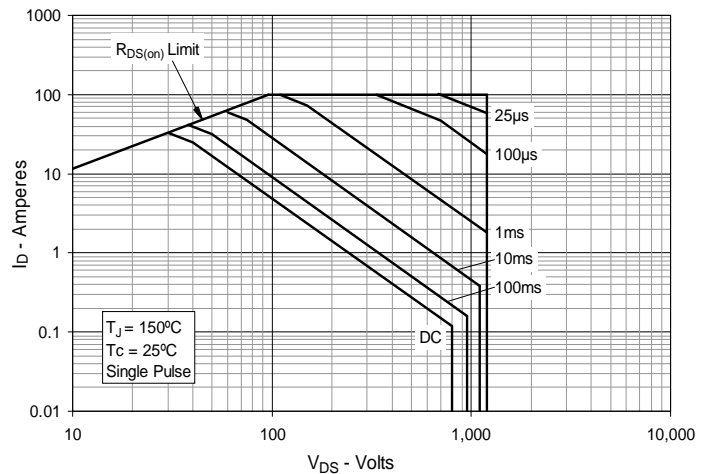


Fig. 13. Maximum Transient Thermal Impedance

